

Fig. 1 Dependence of etch rate of SiO₂ films using HF plasma on substrate temperature.

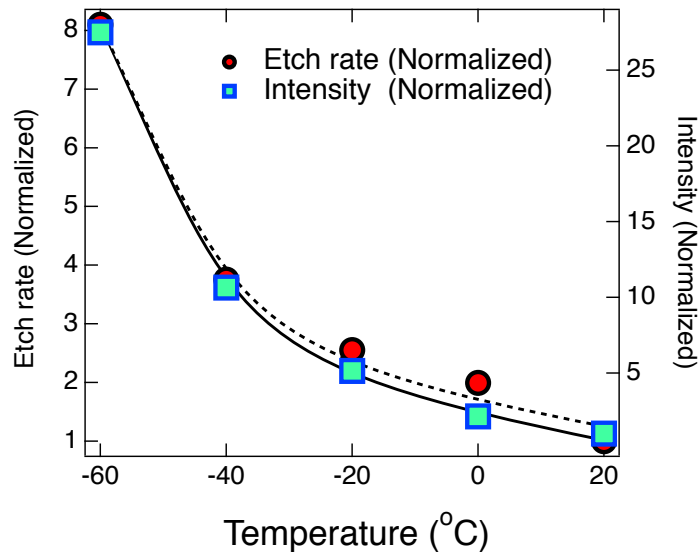


Fig. 2 Dependence of etch rate of SiO₂ and absorbance intensity of the HF-related molecules obtained by ATR-FTIR on substrate temperature. The curves are normalized with the values acquired at 20 °C.